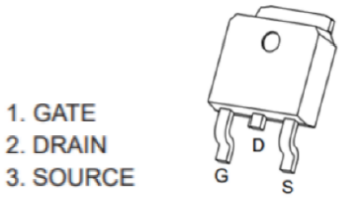
GPM100N03LTF

30V N-Channel MOSFET

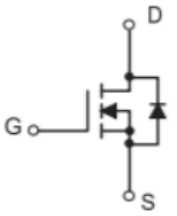
Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	11mΩ@10V	30A
	14mΩ@4.5V	

TO-252-2L



Schematic diagram



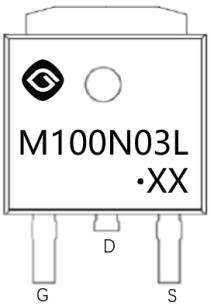
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Power Switching Application

MARKING:



M100N03L = Device Code

XX = Date Code

Solid Dot = Green Indicater

ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	30	V
Gate - Source Voltage		V_{GS}	±20	V
Continuous Drain Current[1]	T_C = 25℃	I_D	30	A
	T_C = 100℃		19	
Pulsed Drain Current[2]		I_{DM}	120	A
Single Pulsed Avalanche Current[3]		I_{AS}	12	A
Single Pulsed Avalanche Energy[3]		E_{AS}	37	mJ
Power Dissipation[5]	T_C = 25℃	P_D	25	W
Thermal Resistance from Junction to Ambient[6]		$R_{\theta JA}$	75	℃/W
Thermal Resistance from Junction to Case		$R_{\theta JC}$	4.9	℃/W
Junction Temperature		T_J	150	℃
Storage Temperature		T_{STG}	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 30V, V_{GS} = 0V			1	μA
Gate - Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics[4]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.0	1.4	3.0	V
Drain-source On-resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D = 20A		11	13	mΩ
		V_{GS} = 4.5V, I_D = 10A		14	22	
Forward Transconductance	g_{FS}	V_{DS} = 10V, I_D = 10A		16		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} = 15V, V_{GS} = 0V, f = 1MHz		847		pF
Output Capacitance	C_{oss}			107		
Reverse Transfer Capacitance	C_{rss}			87		
Gate Resistance	R_g	V_{DS} = 0V, V_{GS} = 0V		2.4		Ω
Switching Characteristics						
Total Gate Charge	Q_g	V_{DS} =25V, V_{GS} = 10V, I_D = 20A		18.8		nC
Gate-source Charge	Q_{gs}			2.2		
Gate-drain Charge	Q_{gd}			5.4		
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 15V, V_{GS} = 10V, I_D = 30A R_G = 1.6Ω		3		ns
Turn-on Rise Time	t_r			3		
Turn-off Delay Time	$t_{d(off)}$			12		
Turn-off Fall Time	t_f			3		
Source - Drain Diode Characteristics						
Diode Forward Voltage[4]	V_{SD}	V_{GS} = 0V, I_S = 1.7A			1.2	V

Notes :

1.The maximum current rating is limited by package.And device mounted on a large heatsink

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

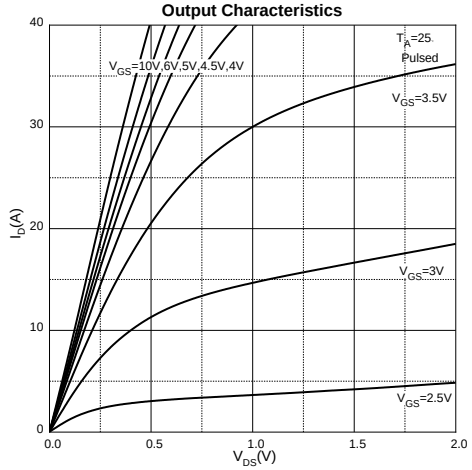
3.E_{AS} condition: V_{DD} = 15V,V_{GS} = 10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°℃.

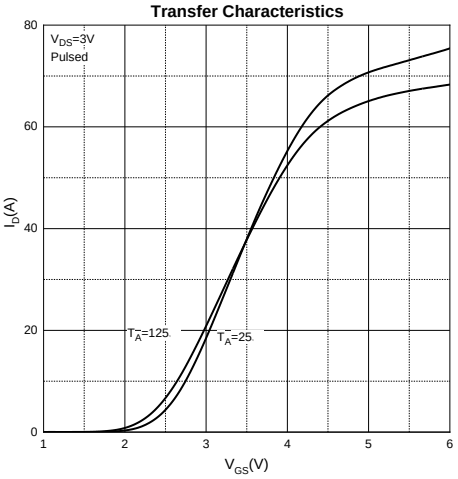
4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

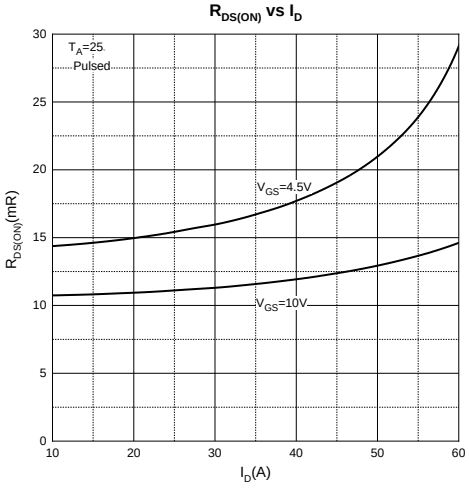
5.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

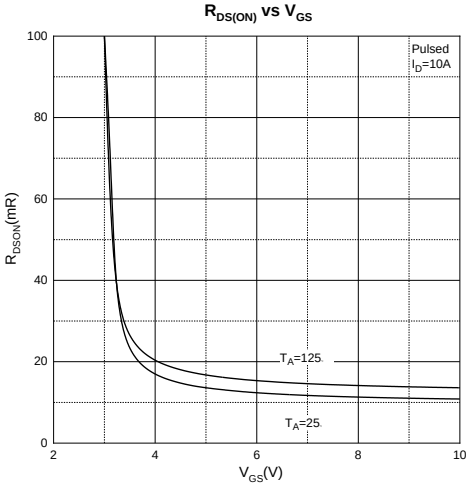
6.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

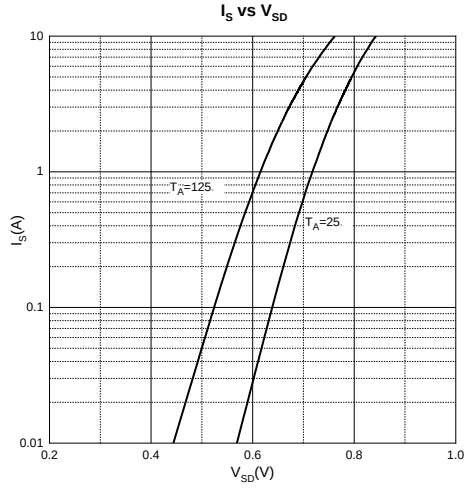
Typical Characteristics

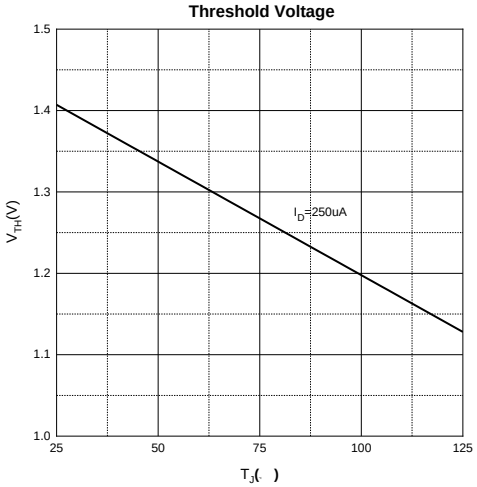




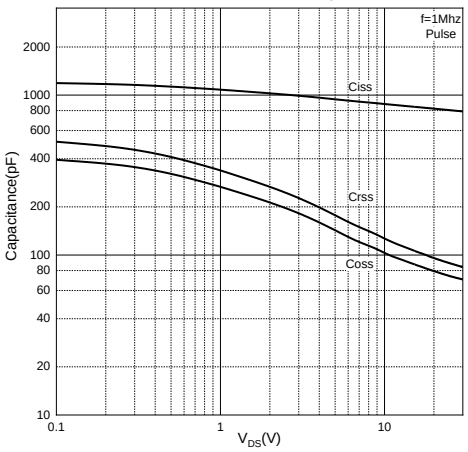




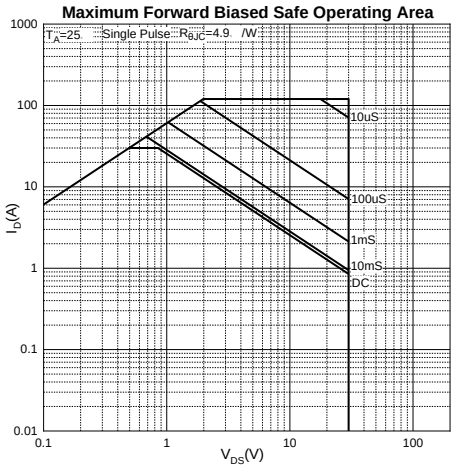




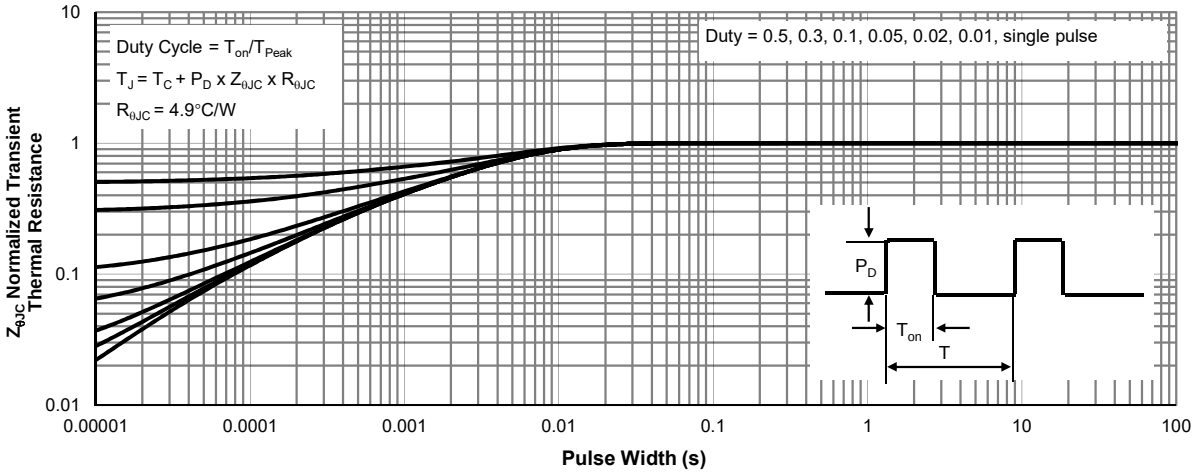
Capacitance vs V_{DS}



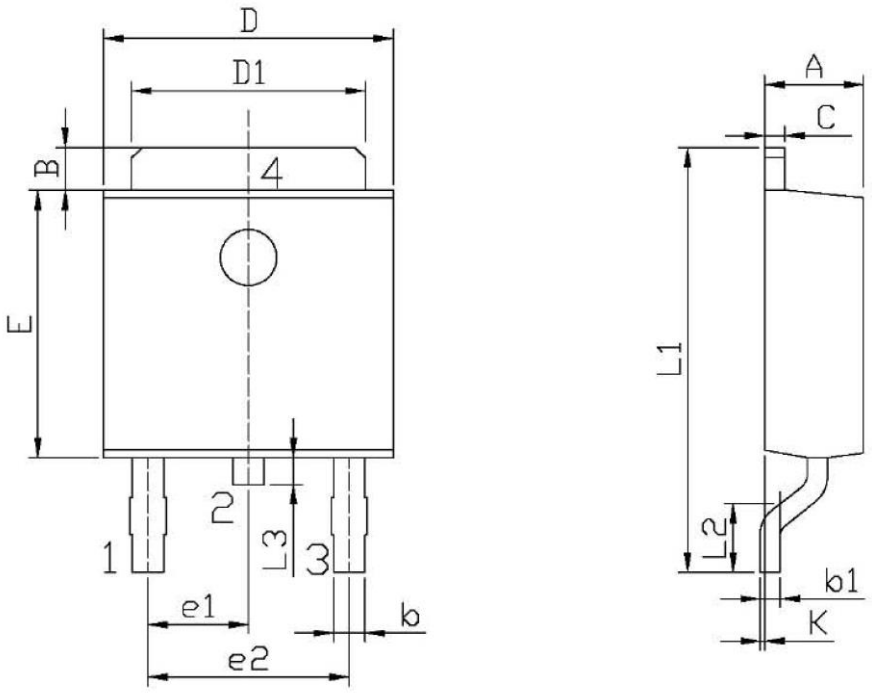
Maximum Forward Biased Safe Operating Area



Normalized Transient Thermal Impedance vs Pulse Width



TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
B	0.950	1.250	0.037	0.049
b	0.500	0.700	0.020	0.028
b1	0.450	0.550	0.018	0.022
C	0.450	0.550	0.018	0.022
D	6.450	6.750	0.254	0.266
D1	5.100	5.500	0.201	0.217
E	5.950	6.250	0.234	0.246
e1	2.240	2.340	0.088	0.092
e2	4.430	4.730	0.174	0.186
L1	9.450	9.950	0.372	0.392
L2	1.250	1.750	0.049	0.069
L3	0.600	0.900	0.024	0.035
K	0.000	0.100	0.000	0.004